

Jaroslav Z Domagala

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

241
papers

2,267
citations

24
h-index

34
g-index

259
ext. papers

2,487
ext. citations

2.6
avg, IF

4.24
L-index

#	Paper	IF	Citations
241	Structural defects in MBE-grown CdTe-basing heterojunctions designed for photovoltaic applications. <i>Semiconductor Science and Technology</i> , 2021 , 36, 045022	1.8	0
240	Phase-transition critical thickness of rocksalt MgZnO layers. <i>Journal of Chemical Physics</i> , 2021 , 154, 154701	9.9	1
239	Magnetoelastic interactions and magnetic damping in CoFeMnSi and CoFeGaGe Heusler alloys thin films for spintronic applications. <i>Scientific Reports</i> , 2021 , 11, 7608	4.9	3
238	Signatures of dephasing by mirror-symmetry breaking in weak-antilocalization magnetoresistance across the topological transition in $\text{Pb}_{1-x}\text{Sn}_x\text{Se}$. <i>Physical Review B</i> , 2021 , 103,	3.3	2
237	Strain relaxation in InGaN/GaN epilayers by formation of V-pit defects studied by SEM, XRD and numerical simulations. <i>Journal of Applied Crystallography</i> , 2021 , 54, 62-71	3.8	2
236	CdTe-based crystals with Mg, Se, or Mn as materials for X and gamma ray detectors: Selected physical properties. <i>Progress in Crystal Growth and Characterization of Materials</i> , 2021 , 100543	3.5	1
235	Rocksalt ZnMgO alloys for ultraviolet applications: Origin of band-gap fluctuations and direct-indirect transitions. <i>Physical Review B</i> , 2020 , 101,	3.3	9
234	Hydrostatic pressure influence on TC in (Ga,Mn)As. <i>Physical Review B</i> , 2020 , 101,	3.3	1
233	Crystal field model simulations of magnetic response of pairs, triplets and quartets of Mn^{3+} ions in GaN. <i>New Journal of Physics</i> , 2020 , 22, 123016	2.9	1
232	Effect of rapid thermal annealing on damage of silicon matrix implanted by low-energy rhenium ions. <i>Journal of Alloys and Compounds</i> , 2020 , 846, 156433	5.7	
231	The effect of transglutaminase on colloidal stability of milk proteins. <i>Journal of Food Measurement and Characterization</i> , 2019 , 13, 2339-2346	2.8	5
230	Experimental search for the origin of low-energy modes in topological materials. <i>Physical Review B</i> , 2019 , 100,	3.3	8
229	Homoepitaxial growth by halide vapor phase epitaxy of semi-polar GaN on ammonothermal seeds. <i>Japanese Journal of Applied Physics</i> , 2019 , 58, SC1030	1.4	6
228	Effects of impurity band in heavily doped ZnO:HCl. <i>Physica B: Condensed Matter</i> , 2019 , 553, 174-181	2.8	7
227	Nature and spatial distribution of extended defects in Czochralski-grown $\text{Ca}_3\text{RE}_2(\text{BO}_3)_4$ (RE = Y, Gd) orthoborate single crystals. <i>Journal Physics D: Applied Physics</i> , 2019 , 52, 055102	3	2
226	Impact of substrate temperature on magnetic properties of plasma-assisted molecular beam epitaxy grown (Ga,Mn)N. <i>Journal of Alloys and Compounds</i> , 2018 , 747, 946-959	5.7	13
225	Investigation of $\text{Cd}_{1-x}\text{Mg}_x\text{Te}$ as possible materials for X and gamma ray detectors. <i>Journal of Crystal Growth</i> , 2018 , 491, 73-76	1.6	7

224	Cubic anisotropy in (Ga,Mn)As layers: Experiment and theory. <i>Physical Review B</i> , 2018 , 97,	3.3	9
223	Band structure evolution and the origin of magnetism in (Ga,Mn)As: From paramagnetic through superparamagnetic to ferromagnetic phase. <i>Physical Review B</i> , 2018 , 97,	3.3	14
222	Semiconductor crystals based on CdTe with Se \square Some structural and optical properties. <i>Journal of Crystal Growth</i> , 2018 , 498, 405-410	1.6	2
221	Basic ammonothermal growth of Gallium Nitride \square State of the art, challenges, perspectives. <i>Progress in Crystal Growth and Characterization of Materials</i> , 2018 , 64, 63-74	3.5	51
220	Equation of State and Amorphization of CaR(VO) (R = La, Nd, Gd): A Combined High-Pressure X-ray Diffraction and Raman Spectroscopy Study. <i>Inorganic Chemistry</i> , 2018 , 57, 13115-13127	5.1	4
219	Influence of substrate temperature on incorporation of magnesium into Zn _{1-x} Mg _x O layers growth by molecular beam epitaxy. <i>Journal of Alloys and Compounds</i> , 2018 , 766, 398-401	5.7	1
218	Comparison of the structural properties of Zn-face and O-face single crystal homoepitaxial ZnO epilayers grown by RF-magnetron sputtering. <i>Journal of Applied Physics</i> , 2017 , 121, 015304	2.5	2
217	Monolithic cyan \square violet InGaN/GaN LED array. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2017 , 214, 1600815	1.6	6
216	Crystal Growth and Glass-Like Thermal Conductivity of Ca ₃ RE ₂ (BO ₃) ₄ (RE = Y, Gd, Nd) Single Crystals. <i>Crystals</i> , 2017 , 7, 88	2.3	12
215	Photoconductive and electro-optic effects in (Cd,Mg)Te single crystals measured in an experiment-on-chip configuration. <i>Applied Physics Letters</i> , 2017 , 111, 011108	3.4	7
214	Arrangement of GaN nanowires on Si(001) substrates studied by X-ray diffraction: Importance of silicon nitride interlayer. <i>Applied Surface Science</i> , 2017 , 425, 1014-1019	6.7	7
213	Experimental evidence for topological surface states wrapping around a bulk SnTe crystal. <i>Physical Review B</i> , 2017 , 96,	3.3	14
212	Novel Quaternary Dilute Magnetic Semiconductor (Ga,Mn)(Bi,As): Magnetic and Magneto-Transport Investigations. <i>Journal of Superconductivity and Novel Magnetism</i> , 2017 , 30, 825-829	1.5	4
211	Influence of edge-grown HVPE GaN on the structural quality of c-plane oriented HVPE-GaN grown on ammonothermal GaN substrates. <i>Journal of Crystal Growth</i> , 2016 , 456, 80-85	1.6	16
210	Thermally activated decomposition of (Ga,Mn)As thin layer at medium temperature post growth annealing. <i>Journal of Physics: Conference Series</i> , 2016 , 712, 012114	0.3	1
209	Hybrid reciprocal lattice: application to layer stress determination in GaAlN/GaN(0001) systems with patterned substrates. <i>Journal of Applied Crystallography</i> , 2016 , 49, 798-805	3.8	10
208	Suppression of extended defects propagation in a laser diodes structure grown on (20-21) GaN. <i>Semiconductor Science and Technology</i> , 2016 , 31, 035001	1.8	6
207	Influence of milk protein cross-linking by transglutaminase on the rennet coagulation time and the gel properties. <i>Journal of the Science of Food and Agriculture</i> , 2016 , 96, 3500-7	4.3	23

206	Correlation of optical and structural properties of GaN/AlN multi-quantum wells <i>Ab initio</i> and experimental study. <i>Journal of Applied Physics</i> , 2016 , 119, 015703	2.5	21
205	Properties of InGaN/GaN multiquantum wells grown on semipolar (20-21) substrates with different miscuts. <i>Journal of Crystal Growth</i> , 2015 , 423, 28-33	1.6	2
204	High power nitride laser diodes grown by plasma assisted molecular beam epitaxy. <i>Journal of Crystal Growth</i> , 2015 , 425, 398-400	1.6	13
203	Optical properties of pure and Ce ³⁺ doped gadolinium gallium garnet crystals and epitaxial layers. <i>Journal of Luminescence</i> , 2015 , 164, 31-37	3.8	12
202	n-ZnO/p-4H-SiC diode: Structural, electrical, and photoresponse characteristics. <i>Applied Physics Letters</i> , 2015 , 107, 101105	3.4	9
201	Magnetic anisotropy induced by crystal distortion in Ge _{1-x} Mn _x Te/PbTe//KCl (001) ferromagnetic semiconductor layers. <i>Journal of Applied Physics</i> , 2015 , 118, 113905	2.5	4
200	Influence of GaN substrate crystallographic quality on the intensity of AlGaIn epitaxial layer X-ray diffraction peaks. <i>Crystal Research and Technology</i> , 2015 , 50, 759-763	1.3	1
199	Impact of bismuth incorporation into (Ga,Mn)As thin films on their structural and magnetic properties. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2015 , 12, 1152-1155		2
198	Observation of topological crystalline insulator surface states on (111)-oriented Pb _{1-x} Sn _x Se films. <i>Physical Review B</i> , 2014 , 89,	3.3	53
197	Effect of low-temperature annealing on the electronic- and band-structures of (Ga,Mn)As epitaxial layers. <i>Journal of Applied Physics</i> , 2014 , 115, 012009	2.5	8
196	High-Resolution X-Ray Diffraction Studies on MBE-Grown p-ZnTe/n-CdTe Heterojunctions for Solar Cell Applications. <i>Acta Physica Polonica A</i> , 2014 , 126, 1083-1086	0.6	1
195	Magnetic and Magneto-Transport Characterization of (Ga,Mn)(Bi,As) Epitaxial Layers. <i>Acta Physica Polonica A</i> , 2014 , 126, 1121-1124	0.6	1
194	Ferromagnetism and the electronic band structure in (Ga,Mn)(Bi,As) epitaxial layers. <i>Applied Physics Letters</i> , 2014 , 105, 072402	3.4	6
193	Electronic- and band-structure evolution in low-doped (Ga,Mn)As. <i>Journal of Applied Physics</i> , 2013 , 114, 053710	2.5	6
192	Growth and Characterization of (Cd, Mn)Te. <i>IEEE Transactions on Nuclear Science</i> , 2013 , 60, 3805-3814	1.7	6
191	Non-periodicity of peak-to-peak distances in x-ray diffraction spectrums from perfect superlattices. <i>Journal of Applied Physics</i> , 2013 , 113, 064302	2.5	3
190	Structural characterization of the epitaxially grown core-shell ZnTe/ZnMgTe nanowires. <i>Radiation Physics and Chemistry</i> , 2013 , 93, 111-116	2.5	
189	Formation of two-dimensionally confined superparamagnetic (Mn, Ga)As nanocrystals in high-temperature annealed (Ga, Mn)As/GaAs superlattices. <i>Journal of Physics Condensed Matter</i> , 2013 , 25, 196005	1.8	4

188	One-dimensional defect distribution along needle-shaped PrVO ₄ single crystals grown by the slow-cooling method. <i>Radiation Physics and Chemistry</i> , 2013 , 93, 174-183	2.5	
187	Structural analysis of epitaxial NbTiN films 2013 ,		1
186	Czochralski Growth and Optical Properties of (Lu _x Gd _{1-x}) ₂ SiO ₅ Solid Solution Crystals Single Doped with Sm ³⁺ and Dy ³⁺ . <i>Acta Physica Polonica A</i> , 2013 , 124, 321-328	0.6	1
185	Triclinic deformation of InGaN layers grown on vicinal surface of GaN (00.1) substrates. <i>Journal of Applied Physics</i> , 2013 , 114, 113512	2.5	10
184	Characterization of the Nonpolar GaN Substrate Obtained by Multistep Regrowth by Hydride Vapor Phase Epitaxy. <i>Applied Physics Express</i> , 2012 , 5, 011001	2.4	6
183	Molecular beam epitaxial growth and magnetotransport properties of GaMnAs. <i>Science and Technology of Atomic, Molecular, Condensed Matter and Biological Systems</i> , 2012 , 2, 21-43		2
182	Hydrogen Sensing Properties of Thin NiO Films Deposited by RF Sputtering. <i>Procedia Engineering</i> , 2012 , 47, 746-749		17
181	Influence of GaN substrate off-cut on properties of InGaN and AlGaIn layers. <i>Crystal Research and Technology</i> , 2012 , 47, 321-328	1.3	28
180	Role of beryllium doping in strain changes in II-type InAs/GaSb superlattice investigated by high resolution X-ray diffraction method. <i>Applied Physics A: Materials Science and Processing</i> , 2012 , 108, 491-496	2.6	8
179	Lateral Control of Indium Content and Wavelength of III-Nitride Diode Lasers by Means of GaN Substrate Patterning. <i>Applied Physics Express</i> , 2012 , 5, 021001	2.4	21
178	Fabrication and Characterization of n-ZnO/p-SiC Heterojunction Diode. <i>Materials Science Forum</i> , 2012 , 717-720, 1323-1326	0.4	
177	Influence of Thermal and Gamma Radiation on Electrical Properties of Thin NiO Films Formed by RF Sputtering. <i>Procedia Engineering</i> , 2011 , 25, 367-370		4
176	An XANES and XES investigation of the electronic structure of indium rich In _x Ga _{1-x} N films. <i>Journal of Alloys and Compounds</i> , 2011 , 509, 9528-9535	5.7	4
175	Structural and magnetic properties of nanoclusters in GaMnAs granular layers. <i>Journal of Solid State Chemistry</i> , 2011 , 184, 1530-1539	3.3	8
174	Structural and magnetic properties of GaAs:(Mn,Ga)As granular layers. <i>Physica Status Solidi (B): Basic Research</i> , 2011 , 248, 1609-1614	1.3	6
173	Structural defects and cathodoluminescence of In _x Ga _{1-x} N layers. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2011 , 8, 2248-2250		5
172	Structural and magnetic properties of GaSb:MnSb granular layers. <i>Radiation Physics and Chemistry</i> , 2011 , 80, 1051-1057	2.5	4
171	Photoreflectance study of the fundamental optical properties of (Ga,Mn)As epitaxial films. <i>Physical Review B</i> , 2011 , 83,	3.3	18

170	Voids and Mn-rich inclusions in a (Ga,Mn)As ferromagnetic semiconductor investigated by transmission electron microscopy. <i>Journal of Applied Physics</i> , 2011 , 109, 083546	2.5	13
169	Formation process and superparamagnetic properties of (Mn,Ga)As nanocrystals in GaAs fabricated by annealing of (Ga,Mn)As layers with low Mn content. <i>Physical Review B</i> , 2011 , 84,	3.3	22
168	Influence of a GaN Cap Layer on the Morphology and the Physical Properties of Embedded Self-Organized InN Quantum Dots on GaN(0001) Grown by MetalOrganic Vapour Phase Epitaxy. <i>Japanese Journal of Applied Physics</i> , 2011 , 50, 031004	1.4	5
167	. <i>IEEE Transactions on Nuclear Science</i> , 2011 , 58, 347-353	1.7	12
166	Ultrathin NbN Films for Superconducting Single-Photon Detectors. <i>Acta Physica Polonica A</i> , 2011 , 120, 200-203	0.6	7
165	Capability of Semiconducting NiO Films in Gamma Radiation Dosimetry. <i>Acta Physica Polonica A</i> , 2011 , 120, A-69-A-72	0.6	2
164	Epitaxial ZnO Films Grown at Low Temperature for Novel Electronic Application. <i>Acta Physica Polonica A</i> , 2011 , 120, A-7-A-10	0.6	8
163	Technology of Ultrathin NbN and NbTiN Films for Superconducting Photodetectors. <i>Acta Physica Polonica A</i> , 2011 , 120, A-76-A-79	0.6	8
162	Tilt of InGaN layers on miscut GaN substrates. <i>Physica Status Solidi - Rapid Research Letters</i> , 2010 , 4, 142-144	1.4	9
161	Ion-Implantation Control of Ferromagnetism in (Ga,Mn)As Epitaxial Layers. <i>Journal of Electronic Materials</i> , 2010 , 39, 794-798	1.9	3
160	Monocrystalline Cd _{0.2} Zn _{0.8} Te solid solution obtained by self-selecting vapour growth. <i>Crystal Research and Technology</i> , 2010 , 45, 895-898	1.3	2
159	(Cd,Mn)Te detectors for characterization of X-ray emissions generated during laser-driven fusion experiments. <i>Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment</i> , 2010 , 624, 649-655	1.2	7
158	Monocrystalline zinc oxide films grown by atomic layer deposition. <i>Thin Solid Films</i> , 2010 , 518, 4556-4559	2.2	33
157	Comparison of dimethylzinc and diethylzinc as precursors for monocrystalline zinc oxide grown by atomic layer deposition method. <i>Physica Status Solidi (B): Basic Research</i> , 2010 , 247, 1699-1701	1.3	12
156	Zinc oxide grown by atomic layer deposition as a material for novel 3D electronics. <i>Physica Status Solidi (B): Basic Research</i> , 2010 , 247, 1611-1615	1.3	15
155	Defect Structure of High-Temperature-Grown GaMnSb/GaSb. <i>Acta Physica Polonica A</i> , 2010 , 117, 341-343	0.6	8
154	Spatially resolved x-ray diffraction study of GaSb layers grown laterally on SiO ₂ -masked GaAs substrates. <i>Journal of Applied Physics</i> , 2009 , 106, 043521	2.5	3
153	Structural and magnetic properties of the molecular beam epitaxy grown MnSb layers on GaAs substrates. <i>Journal of Applied Physics</i> , 2009 , 106, 083524	2.5	6

152	Spatially resolved X-ray diffraction as a tool for strain analysis in laterally modulated epitaxial structures. <i>Crystal Research and Technology</i> , 2009 , 44, 1089-1094	1.3	1
151	X-ray characterization of catalytically grown ZnTe and ZnMgTe nanowires. <i>Radiation Physics and Chemistry</i> , 2009 , 78, S120-S124	2.5	6
150	Effect of processing on microstructure of Si:Mn. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2009 , 159-160, 99-102	3.1	7
149	Spontaneous stratification of InGaN layers and its influence on optical properties. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2009 , 6, S433-S436		11
148	Structural perfection of InGaN layers and its relation to photoluminescence. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2009 , 6, 2626-2631		13
147	Structural properties of (Ga,Mn)Sb thin films on GaAs(111)A substrate. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2009 , 6, 2792-2794		
146	Effect of AlN interlayers in the structure of GaN-on-Si grown by plasma-assisted MBE. <i>Journal of Crystal Growth</i> , 2009 , 311, 2010-2015	1.6	7
145	Creation of MnAs nanoclusters during processing of GaMnAs. <i>Radiation Physics and Chemistry</i> , 2009 , 78, S116-S119	2.5	5
144	ZnO by ALD - Advantages of the Material Grown at Low Temperature. <i>Acta Physica Polonica A</i> , 2009 , 116, 814-817	0.6	18
143	Rocking Curve Imaging Studies of Laterally Overgrown GaAs and GaSb Epitaxial Layers. <i>Acta Physica Polonica A</i> , 2009 , 116, 976-978	0.6	1
142	Structure Deformation in GdCOB Single Crystals Grown by the Czochralski Method. <i>Crystal Growth and Design</i> , 2008 , 8, 3253-3256	3.5	10
141	Effects of Stress-relieving AlN Interlayers in GaN-on-Si Grown by Plasma-assisted Molecular Beam Epitaxy. <i>Materials Research Society Symposia Proceedings</i> , 2008 , 1068, 1		
140	Comparative study on stress in AlGaIn/GaN HEMT structures grown on 6H-SiC, Si and on composite substrates of the 6H-SiC/poly-SiC and Si/poly-SiC. <i>Journal of Physics: Conference Series</i> , 2008 , 100, 042035	0.3	1
139	X-ray diffraction micro-imaging of strain in laterally overgrown GaAs layers. Part II: analysis of multi-stripe and fully overgrown layers. <i>Applied Physics A: Materials Science and Processing</i> , 2008 , 91, 609-614	2.6	3
138	X-ray diffraction micro-imaging of strain in laterally overgrown GaAs layers. Part I: analysis of a single GaAs stripe. <i>Applied Physics A: Materials Science and Processing</i> , 2008 , 91, 601-607	2.6	8
137	X-ray diffractometry and topography of lattice plane curvature in thermally deformed Si wafer. <i>Journal of Synchrotron Radiation</i> , 2008 , 15, 96-9	2.4	5
136	Spatially Resolved X-ray Diffraction Technique for Crystallographic Quality Inspection of Semiconductor Microstructures. <i>Acta Physica Polonica A</i> , 2008 , 114, 1101-1107	0.6	3
135	Epitaxial Growth and Optical Properties of PbTe/CdTe Semiconductor Heterostructures. <i>Acta Physica Polonica A</i> , 2008 , 114, 1391-1396	0.6	6

134	Influence of Ion Implantation on Magnetic Structural and Optical Properties of (Ga,Mn)As Epitaxial Films. <i>Acta Physica Polonica A</i> , 2008 , 114, 1445-1450	0.6	1
133	Magnetic and Structural Properties of Ferromagnetic GeMnTe Layers. <i>Springer Proceedings in Physics</i> , 2008 , 11-14	0.2	
132	MBE Growth and Properties of ZnTe- and CdTe-Based Nanowires. <i>Journal of the Korean Physical Society</i> , 2008 , 53, 3055-3063	0.6	24
131	Antioxidant activity of some phenolic constituents from green pepper (<i>Piper nigrum</i> L.) and fresh nutmeg mace (<i>Myristica fragrans</i>). <i>Food Chemistry</i> , 2007 , 101, 515-523	8.5	90
130	Hybrid reciprocal space for X-ray diffraction in epitaxial layers. <i>Journal of Applied Crystallography</i> , 2007 , 40, 546-551	3.8	11
129	A new method of strain determination in partially relaxed thin films. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2007 , 4, 3048-3055		
128	Analysis of biaxial strain in InN(0001) epilayers grown by molecular beam epitaxy. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2007 , 204, 1996-1999	1.6	2
127	Modification of the local atomic structure around Mn atoms in (Ga, Mn)As layers by high temperature annealing. <i>Journal of Physics Condensed Matter</i> , 2007 , 19, 496205	1.8	13
126	Tilt and dislocations in epitaxial laterally overgrown GaAs layers. <i>Journal of Applied Physics</i> , 2007 , 101, 013508	2.5	11
125	Mn enriched surface of annealed (GaMn)As layers annealed under arsenic capping. <i>Physical Review B</i> , 2007 , 75,	3.3	11
124	Nitride based laser diodes on substrates with patterned AlN mask. <i>Applied Physics Letters</i> , 2007 , 91, 221103	1.03	4
123	Imaging of strain in laterally overgrown GaAs layers by spatially resolved x-ray diffraction. <i>Applied Physics Letters</i> , 2007 , 90, 241904	3.4	13
122	Structure of Magnetically Ordered Si:Mn. <i>Solid State Phenomena</i> , 2007 , 131-133, 327-332	0.4	1
121	Growth and Properties of ZnMnTe Nanowires. <i>Acta Physica Polonica A</i> , 2007 , 112, 351-356	0.6	3
120	Structural properties of 10 ⁴ Å thick InN grown on sapphire (0001). <i>Superlattices and Microstructures</i> , 2006 , 40, 246-252	2.8	32
119	Growth of thin AlInN/GaN quantum wells for applications to high-speed intersubband devices at telecommunication wavelengths. <i>Journal of Vacuum Science & Technology B</i> , 2006 , 24, 1505		24
118	Crystal Defects and Strain of Epitaxial InP Layers Laterally Overgrown on Si. <i>Crystal Growth and Design</i> , 2006 , 6, 1096-1100	3.5	9
117	Growth and characterization of AlInN/GaN quantum wells for high-speed intersubband devices at telecommunication wavelengths 2006 ,		3

116	ZnO crystals for substrates in micro and optoelectronic applications. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2006 , 3, 793-796		8
115	Crystallization of free standing bulk GaN by HVPE. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2006 , 3, 1453-1456		8
114	The influence of lattice parameter variation on microstructure of GaN single crystals. <i>Journal of Alloys and Compounds</i> , 2005 , 401, 261-264	5.7	34
113	Postgrowth annealing of (Ga,Mn) As under As capping: An alternative way to increase TC. <i>Applied Physics Letters</i> , 2005 , 86, 112501	3.4	49
112	Strain and defect structure of iron implanted In _{0.53} Ga _{0.47} As using high-resolution X-ray diffraction. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2005 , 239, 414-418	1.2	3
111	The influence of the ion implantation temperature and the dose rate on smart-cut [®] in GaAs. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2005 , 240, 142-145	1.2	6
110	Bowing of epitaxial layers grown on bulk GaN substrates. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2005 , 2, 1259-1264		1
109	An X-ray diffraction study of the structural properties of thick relaxed (100) InGaAs/GaAs heterostructures. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2005 , 2, 1298-1303		
108	Microstructure of III-N semiconductors related to their applications in optoelectronics. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2005 , 2, 1366-1373		1
107	Anisotropic strain relaxation in lattice-mismatched III ^V epitaxial layers. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2005 , 2, 1943-1947		3
106	Strain state of InAlAs/InP layers subjected to high pressure treatment. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2005 , 2, 1948-1952		3
105	Growth by atomic layer epitaxy and characterization of thin films of ZnO. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2005 , 2, 1125-1130		17
104	Microstructure of InGaN quantum wells grown on GaN single crystals and sapphire. <i>Journal Physics D: Applied Physics</i> , 2005 , 38, A89-A92	3	1
103	Self-organized MnAs quantum dots formed during annealing of GaMnAs under arsenic capping. <i>Applied Physics Letters</i> , 2005 , 87, 263114	3.4	15
102	Solid Phase Epitaxy of Ferromagnetic MnAs Layer and Quantum Dots on Annealed GaMnAs. <i>Acta Physica Polonica A</i> , 2005 , 108, 851-858	0.6	
101	Influence of defects on the lattice constant of GaMnAs. <i>Physical Review B</i> , 2004 , 69,	3.3	55
100	Anisotropy of Strain Relaxation in III-V Semiconductor Heterostructures. <i>Defect and Diffusion Forum</i> , 2004 , 230-232, 93-100	0.7	1
99	Misfit strain anisotropy in partially relaxed lattice-mismatched InGaAs/GaAs heterostructures. <i>Journal of Physics Condensed Matter</i> , 2004 , 16, S1-S8	1.8	33

98	Effect of uniform compression on photoluminescence spectra of GaAs layers heavily doped with beryllium. <i>Semiconductors</i> , 2004 , 38, 277-280	0.7	1
97	Effect of annealing on magnetic and magnetotransport properties of Ga _{1-x} MnAs epilayers. <i>Journal of Magnetism and Magnetic Materials</i> , 2004 , 272-276, E1575-E1577	2.8	2
96	Ni ²⁺ level temperature of zinc-blende, MBE-grown MnTe layers: modification by the crystal growth conditions. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2004 , 1, 953-956		2
95	Monocrystalline ZnO films grown by atomic layer epitaxy: growth and characterization. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2004 , 1, 892-895		2
94	Formation of rocking curves for quasi-forbidden reflections in short-periodic superlattices GaAs/AlGaAs. <i>Journal of Applied Crystallography</i> , 2004 , 37, 150-155	3.8	2
93	Monocrystalline thin films of ZnSe and ZnO grown by atomic layer epitaxy. <i>Vacuum</i> , 2004 , 74, 269-272	3.7	10
92	Effect of Mn interstitials on the lattice parameter of Ga _{1-x} MnxAs. <i>Journal of Applied Physics</i> , 2004 , 95, 603-608	2.5	33
91	Monocrystalline ZnO Films on GaN/Al ₂ O ₃ by Atomic Layer Epitaxy in Gas Flow. <i>Chemistry of Materials</i> , 2004 , 16, 1447-1450	9.6	27
90	High-pressure structural and optical properties of wurtzite-type Zn _{1-x} Mg _x Se. <i>Journal of Alloys and Compounds</i> , 2004 , 371, 168-171	5.7	6
89	Contactless growth of uniform Cd _{0.8} Zn _{0.2} Te monocrystals from the vapour. <i>Materials Letters</i> , 2004 , 58, 1781-1783	3.3	5
88	Pressure distribution in a large-anvil pressure cell. <i>Journal of Alloys and Compounds</i> , 2004 , 362, 96-98	5.7	2
87	Pressure-induced defect structure changes in thin AlGaAs layers. <i>Journal of Alloys and Compounds</i> , 2004 , 362, 254-260	5.7	3
86	Influence of high pressure and temperature on defect structure of silicon crystals implanted with N or Si ions. <i>Journal of Alloys and Compounds</i> , 2004 , 362, 275-281	5.7	4
85	Monocrystalline and Polycrystalline ZnO and ZnMnO Films Grown by Atomic Layer Epitaxy - Growth and Characterization. <i>Acta Physica Polonica A</i> , 2004 , 105, 667-673	0.6	8
84	Strain release in InGaAs/In _x Al _{1-x} As/InP heterostructures. <i>Physica B: Condensed Matter</i> , 2003 , 340-342, 1082-1085	2.8	9
83	Ferromagnetic GaMnAs/GaAs superlattices: MBE growth and magnetic properties. <i>Thin Solid Films</i> , 2002 , 412, 122-128	2.2	22
82	X-ray diffraction studies of epitaxial laterally overgrown (ELOG) GaN layers on sapphire substrates. <i>Journal of Crystal Growth</i> , 2002 , 245, 37-49	1.6	6
81	Characterization of Silicon-on-Insulator Structures by High-Resolution X-Ray Diffraction. <i>Journal of the Electrochemical Society</i> , 2002 , 149, G490	3.9	6

80	CdS _x Te _{1-x} : bulk vapour growth, twin formation and the electrical activity of twin boundaries. <i>Journal Physics D: Applied Physics</i> , 2002 , 35, 1997-2007	3	8
79	Nanostructure of Thin Gold Films Investigated by Means of Atomic Force Microscopy and X-Ray Reflectometry Methods. <i>Acta Physica Polonica A</i> , 2002 , 102, 289-294	0.6	1
78	Magnetic Properties of Short Period InGaMnAs/InGaAs Superlattices. <i>Acta Physica Polonica A</i> , 2002 , 102, 687-694	0.6	6
77	Defects and their Electronic Properties in High-Pressure-Annealed SOI Structures Sliced by Hydrogen 2002 , 269-288		8
76	Relaxation of InGaN thin layers observed by X-ray and transmission electron microscopy studies. <i>Journal of Electronic Materials</i> , 2001 , 30, 439-444	1.9	32
75	Depth-influenced structure through permeating polymer membrane using SAXS synchrotron method. <i>Journal of Membrane Science</i> , 2001 , 186, 1-8	9.6	9
74	Defect transformation study in silicon-on-insulator structures by high-resolution X-Ray diffraction. <i>Materials Science in Semiconductor Processing</i> , 2001 , 4, 35-37	4.3	5
73	Stress-induced transformation of defects in homoepitaxial beryllium-doped GaAs thin films. <i>Physica B: Condensed Matter</i> , 2001 , 308-310, 820-822	2.8	5
72	Properties of GaMnAs layers grown by migration enhanced epitaxy at very low substrate temperatures. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2001 , 10, 181-185	3	4
71	Effect of High Temperature-Pressure on GaAs Layers Grown on Vicinal Si Substrates. <i>Crystal Research and Technology</i> , 2001 , 36, 997-1003	1.3	6
70	Structural and magnetic properties of GaMnAs layers with high Mn-content grown by migration-enhanced epitaxy on GaAs(100) substrates. <i>Applied Physics Letters</i> , 2001 , 78, 3271-3273	3.4	56
69	Control of adhesion to the mask of epitaxial laterally overgrown GaAs layers. <i>Journal of Applied Physics</i> , 2001 , 90, 6140-6144	2.5	15
68	Stress-induced transformation of microdefects in neutron irradiated Czochralski silicon. <i>Solid State Sciences</i> , 2001 , 3, 1307-1309		
67	X-ray study of silicon crystal structure changes due to implantation with fast nitrogen ions. <i>Journal of Alloys and Compounds</i> , 2001 , 328, 237-241	5.7	7
66	Low-temperature thermal expansion of Mg ₃ N ₂ . <i>Journal of Alloys and Compounds</i> , 2001 , 328, 272-275	5.7	6
65	Structural changes induced by fast nitrogen ions in GaAs single crystals. <i>Journal of Alloys and Compounds</i> , 2001 , 328, 112-118	5.7	5
64	Strain in hydrogen and oxygen implanted silicon and SOI structures annealed at high pressure. <i>Journal of Alloys and Compounds</i> , 2001 , 328, 181-186	5.7	6
63	Microwave Plasma Etching of GaN in Nitrogen Atmosphere. <i>Physica Status Solidi A</i> , 2000 , 181, 151-155		2

62	Structural properties of MBE grown GaMnAs layers. <i>Thin Solid Films</i> , 2000 , 367, 165-167	2.2	14
61	Effect of stress on interface transformation in thin semiconducting layers. <i>Thin Solid Films</i> , 2000 , 380, 117-119	2.2	6
60	Structural and magnetic properties of molecular beam epitaxy grown GaMnAs layers. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2000 , 18, 1697		52
59	High-pressure high-temperature annealing of ion-implanted GaN films monitored by visible and ultraviolet micro-Raman scattering. <i>Journal of Applied Physics</i> , 2000 , 87, 2736-2741	2.5	30
58	Thermal expansion of bulk and homoepitaxial GaN. <i>Applied Physics Letters</i> , 2000 , 77, 1434-1436	3.4	27
57	Thermal expansion of GaN at low temperatures - a comparison of bulk and homo- and heteroepitaxial layers. <i>MRS Internet Journal of Nitride Semiconductor Research</i> , 2000 , 5, 391-397		
56	Thermal strain in GaAs layers grown by epitaxial lateral overgrowth on Si substrates. <i>Applied Physics Letters</i> , 1999 , 75, 2749-2751	3.4	19
55	Synchrotron x-ray topographic and high-resolution diffraction analysis of mask-induced strain in epitaxial laterally overgrown GaAs layers. <i>Journal of Applied Physics</i> , 1999 , 86, 4298-4303	2.5	15
54	Strain in GaAs layers grown by liquid phase epitaxial lateral overgrowth. <i>Journal of Applied Physics</i> , 1999 , 86, 1965-1969	2.5	18
53	Changes in the microstructure of GaN layers on sapphire upon annealing at high pressure. <i>Thin Solid Films</i> , 1999 , 350, 295-299	2.2	1
52	Parameters of substrates—single crystals of ZnTe and Cd _{1-x} Zn _x Te (x. <i>Journal of Crystal Growth</i> , 1999 , 197, 423-426	1.6	18
51	Epitaxy of ternary nitrides on GaN single crystals. <i>Journal of Crystal Growth</i> , 1999 , 198-199, 1061-1065	1.6	8
50	High-pressure—high-temperature study of Hg _{1-x} Mn _x S. <i>Journal of Alloys and Compounds</i> , 1999 , 286, 208-213	3.7	4
49	Dependence of photoluminescence of silicon on conditions of pressure-annealing. <i>Journal of Alloys and Compounds</i> , 1999 , 286, 258-264	5.7	9
48	Lattice parameters of GaN single crystals, homoepitaxial layers and heteroepitaxial layers on sapphire. <i>Journal of Alloys and Compounds</i> , 1999 , 286, 271-275	5.7	20
47	Direct measurement of the lattice parameter of thick stable zinc-blende MgTe layer. <i>Journal of Alloys and Compounds</i> , 1999 , 286, 276-278	5.7	13
46	Influence of high hydrostatic pressure—high temperature treatment on defect structure of AlGaAs layers. <i>Journal of Alloys and Compounds</i> , 1999 , 286, 279-283	5.7	8
45	Strain relaxation of Al _x Ga _{1-x} N epitaxial layers on GaN and SiC substrates. <i>Journal of Alloys and Compounds</i> , 1999 , 286, 284-288	5.7	6

44	X-ray diffraction and Raman scattering study of near-surface structure perfection of GaAs single crystals after anisotropic etching. <i>Journal of Alloys and Compounds</i> , 1999 , 286, 289-296	5.7	7
43	X-ray and magnetic study of epitaxial W/Gd/W and W/Tb/W thin films. <i>Journal of Alloys and Compounds</i> , 1999 , 286, 333-336	5.7	
42	Study of near-surface layers modified by ion implantation in Si wafers by grazing incidence X-ray reflectometry. <i>Journal of Alloys and Compounds</i> , 1999 , 286, 337-342	5.7	1
41	Single crystals of ZnTe and (Cd,Zn)Te produced by physical vapor transport technique for MBE (substrates) and other applications 1999 ,		1
40	Reciprocal lattice mapping of InGaAs layers grown on InP(001) and GaAs(001) substrates 1999 ,		1
39	Mask-Induced Strain in GaAs Layers Grown by Liquid Phase Epitaxial Lateral Overgrowth. <i>Materials Research Society Symposia Proceedings</i> , 1999 , 570, 273		6
38	Thermal expansion of GaN at low temperatures - a comparison of bulk and homo- and heteroepitaxial layers. <i>Materials Research Society Symposia Proceedings</i> , 1999 , 595, 1		
37	Structural defects and compositional uniformity in CdTe and Cd _{1-x} Zn _x Te crystals grown by a vapour transport technique. <i>Journal of Crystal Growth</i> , 1998 , 191, 673-678	1.6	13
36	Lattice parameter, microhardness and energy gap of bulk Zn _{1-x} Be _x Se alloys. <i>Solid State Communications</i> , 1998 , 107, 735-740	1.6	25
35	X-ray characterisation of Zn _{1-x} CoxS single crystals grown by chemical vapour transport. <i>Journal of Alloys and Compounds</i> , 1998 , 274, 128-135	5.7	3
34	A channeling investigation of the structural modifications in uranium dioxide submitted to swift-ion irradiation and aqueous corrosion. <i>Nuclear Instruments & Methods in Physics Research B</i> , 1998 , 136-138, 465-470	1.2	11
33	Resistive and structural properties of La _{1.85} Sr _{0.15} Cu _{1-x} ZnyO ₄ films. <i>Applied Physics Letters</i> , 1998 , 73, 2823-2825	3.4	13
32	Microscopic bending of GaAs layers grown by epitaxial lateral overgrowth. <i>Journal of Applied Physics</i> , 1998 , 84, 6937-6939	2.5	20
31	Optical and Structural Properties of Zn _{1-x} BexSe Mixed Crystals. <i>Acta Physica Polonica A</i> , 1998 , 94, 309-312	3.6	1
30	MBE Growth and Properties of GaMnAs(100) Films. <i>Acta Physica Polonica A</i> , 1998 , 94, 509-513	0.6	11
29	Properties of Fe Doped HgS under Hydrostatic Pressure. <i>Acta Physica Polonica A</i> , 1998 , 94, 570-574	0.6	1
28	PVT-Grown Single Crystals of Cd _{1-x} Zn _x Te (x=0.25) and ZnTe as Substrates for Epitaxy. <i>Acta Physica Polonica A</i> , 1998 , 94, 441-445	0.6	
27	Influence of Free Charge on the Lattice Parameters of GaN and Other Semiconductors. <i>Materials Research Society Symposia Proceedings</i> , 1997 , 468, 311		4

26	Influence of free electrons and point defects on the lattice parameters and thermal expansion of gallium nitride. <i>Nuovo Cimento Della Societa Italiana Di Fisica D - Condensed Matter, Atomic, Molecular and Chemical Physics, Biophysics</i> , 1997 , 19, 585-590		2
25	Conductance anomalies in strained quantum wires: the case of PbSe and PbTe. <i>Superlattices and Microstructures</i> , 1997 , 22, 51-55	2.8	7
24	Physical Properties of AlGaAs Epilayers Subjected to High Pressure - High Temperature Treatment. <i>Acta Physica Polonica A</i> , 1997 , 91, 1003-1007	0.6	1
23	Comparative Studies of Surface Roughness of Thin Epitaxial Si Films by Computer Simulations and Experimental X-Ray and Optical Methods. <i>Acta Physica Polonica A</i> , 1997 , 91, 1025-1030	0.6	2
22	Structure and Magnetism of MBE-Grown Co/Cu Multilayers. <i>Acta Physica Polonica A</i> , 1997 , 91, 315-319	0.6	1
21	Study of Si(111) Implanted with As Ions by X-Ray Diffraction and Grazing Incidence Methods. <i>Acta Physica Polonica A</i> , 1997 , 91, 905-910	0.6	1
20	Effect of Doping on Ga _{1-x} Al _x As Structural Properties. <i>Acta Physica Polonica A</i> , 1997 , 91, 911-917	0.6	2
19	Defect Structure of Pressure Treated Czochralski Grown Silicon Investigated by X-Ray Topography and Diffractometry. <i>Acta Physica Polonica A</i> , 1997 , 91, 987-991	0.6	3
18	Anisotropic Lattice Misfit Relaxation in AlGaAs Semi-Bulk Layers Grown on GaAs Substrates by Liquid Phase Electroepitaxy. <i>Acta Physica Polonica A</i> , 1997 , 92, 1092-1096	0.6	1
17	Structural and Electrical Properties of Low Concentration SnTe Layers and PbTe/SnTe Heterostructures Grown by MBE. <i>Acta Physica Polonica A</i> , 1997 , 92, 967-970	0.6	1
16	X-Ray Characterization of GaAs:Zn Gas-transport Grown Whiskers Using Conventional and Synchrotron Sources. <i>Acta Physica Polonica A</i> , 1997 , 91, 997-1002	0.6	
15	Growth by atmospheric pressure OMVPE and X-ray analysis of ZnTe epilayers on III \bar{V} substrates. <i>Journal of Crystal Growth</i> , 1996 , 165, 203-209	1.6	4
14	The microstructure of gallium nitride monocrystals grown at high pressure. <i>Journal of Crystal Growth</i> , 1996 , 169, 235-242	1.6	47
13	Zinc-blende MnTe(111) on BaF ₂ (111) substrates for optical measurements. <i>Applied Physics Letters</i> , 1996 , 68, 3796-3798	3.4	13
12	Influence of redistribution of electrons in the conduction band on the lattice parameters of Al _x Ga _{1-x} As. <i>Applied Physics Letters</i> , 1996 , 69, 3366-3368	3.4	5
11	Oscillations in Reflectivity of Samples with X-ray Waveguide Layers. <i>Acta Physica Polonica A</i> , 1996 , 89, 323-328	0.6	4
10	Transformation of AlGaAs/GaAs Interface under Hydrostatic Pressure. <i>Acta Physica Polonica A</i> , 1996 , 89, 405-409	0.6	6
9	Temperature study of lattice constants and Raman scattering of SrLaGaO ₄ single crystal. <i>Solid State Communications</i> , 1995 , 96, 785-788	1.6	13

8	Lattice dilation by free electrons in heavily doped GaAs:Si. <i>Applied Physics Letters</i> , 1995 , 67, 539-541	3.4	30
7	Lattice constants and thermal expansion of Al _x Ga _{1-x} As:Te. <i>Journal of Applied Physics</i> , 1995 , 78, 6994-6998	0.5	7
6	Cubic MnTe - Growth by Molecular Beam Epitaxy and Basic Structural Characterization. <i>Acta Physica Polonica A</i> , 1995 , 87, 433-436	0.6	6
5	Lattice Constant of Doped Semiconductor. <i>Acta Physica Polonica A</i> , 1995 , 88, 837-840	0.6	32
4	MBE Growth and Characterization of Cubic MnTe(111) on BaF ₂ Substrates. <i>Acta Physica Polonica A</i> , 1995 , 88, 982-984	0.6	
3	Determination of Ga _{1-x} Al _x As epitaxial layer composition by X-ray intensity measurements of quasi-forbidden reflections. <i>Journal of Crystal Growth</i> , 1993 , 126, 168-173	1.6	1
2	X-Ray and Electron-Optical Characterization of ZnSe(Co) Crystal with Natural Face. <i>Acta Physica Polonica A</i> , 1993 , 83, 759-768	0.6	1
1	Thermal properties of CaNdAlO ₄ and SrLaAlO ₄ single crystals. <i>Materials Research Bulletin</i> , 1992 , 27, 483-490	4.0	31